	-		-			•	
	_	umber	Hit		DB ·	Time stamp	·]
	1	•	197	- (Direction of the sub-time of the	USPAT;	2004/05/18	
	١.,	•	: 1	(nucleat\$ seed\$))	US-PGPUB	16:06	
	2		39:	9 (((nitride "si.sub.3 n.sub.4") with	USPAT;		
				(nucleat\$ seed\$))) and (implant\$)		2004/05/18	
	3		288	((((nitride "si.sub.3 n.sub.4") with	US-PGPUB	16:04	·
			20.	(nucleate salation) with	USPAT;	2004/05/18	
				(nucleat\$ seed\$))) and (implant\$)) not	US-PGPUB	16:07	- 1
	4		204	(@ad>20010723 or @rlad>20010723)		İ	
	1 3		204	- 1	USPAT;	2004/05/18	1
				(nucleat\$ seed\$))) and (implant\$)) not	US-PGPUB	16:07	
	İ			(@ad>20010723 or @rlad>20010723)) and		120.07	
	_			nucleatș			
	5		160757		USPAT;	2004/05/110	- 1
	١.			(nucleat\$ seed\$)) same2 implant\$	1 '	2004/05/18	
	6		62	((nitride "si.sub.3 n.sub.4") with	US-PGPŲB	16:07	
			'	(nucleat\$ seed\$)) same implant\$	USPAT;	2004/05/18	
	7		4'5	(Indefeat) Seeds)) same implants	US-PGPUB	18:35	
•	•		13		USPAT;	2004/05/18	<i>*</i>
				(nucleat\$ seed\$)) same implant\$) not	US-PGPUB	16:07	1
			£ .	(@ad>20010723 or @rlad>20010723)			
	8		. 34	((((nitride "si.sub.3 n.sub.4") with	USPAT;	2004/05/18	
.				(nucleat\$ seed\$)) same implant\$) not	US-PGPUB		. [
		٠.		1 (@ad>20010723 or @rlad>20010723); and	OD-EGEOR .	16:17	
.			1	nucleat\$			
. 4	. 9		11		1:	1	. 1
	• •	: - :		(nicleats goods)) goods	USPAT;	2004/05/18	
				(nucleat\$ seed\$)) same implant\$) not	US-PGPUB	16:17	
.				(@ad>20010723 or @rlad>20010723)) not			
				(((((nitride "si.sub.3 n.sub.4") with			
				(nucleats seeds)) same implants) not			
ľ			: ,	(@ad>20010723 or @rlad>20010723)) and			
		•		nucleat\$)			
	10		243	(((((nitride "si.sub.3 n.sub.4") with	HODAM		
		*.		(nucleat\$ seed\$))) and (implant\$)) not	USPAT;	2004/05/18	ĺ
- 1				(@ad>20010723 or @rlad>20010723)) not	US-PGPUB	16:20	ľ.
				((/nitride "si	,		ŀ
. [9	(((nitride "si.sub.3 n.sub.4") with			.]
	11		165902	(nucleat\$ seed\$)) same implant\$)			.
- 1			103902	438/\$.ccls. or 257/\$.ccls.	USPAT;	2004/05/18	
	12 .	٠.	1		US-PGPUB	16:21	
	12		197	((((((nitride "si.sub.3 n.sub.4") with	USPAT;	2004/05/18	ľ
1				(nucleat\$ seed\$))) and (implant\$)) not	US-PGPUB		1
				(@ad>20010723 or @rlad>20010723)).not	US-PGPUB	19:09	- 1
- [.	•			(((nitride "si.sub.3 n.sub.4") with			
				(nucleat\$ seed\$)) same implant\$)) and			
		•		(438/\$.ccls. or 257/\$.ccls.)		A	
	13	•	.42	(angles non implants)	•		1.
			1		USPAT;	2004/05/18	
- -	1 4	1.	150	uniform\$) *	US-PGPUB	18:25	
- 1	14		156	'(implant\$) same (nitride with uniform\$)	USPAT;	2004/05/18	
Ι.	1 [-	•		A STATE OF THE STA	US-PGPUB	18:27	
- F	15		2	(implant\$) same (nitride with uniform\$)	USPAT;	2004/05/18	
			1	same (nucleats)	US-PGPUB		
1	16		131	((implant\$) same (nitride with imiforms))		18:26	
				and (438/\$.ccls. or 257/\$.ccls.)	USPAT;	2004/05/18	
	L7		7	(implant\$) same (nitride with uniform\$)	US-PGPUB	18:26	
ŀ		.	'	same angle\$	USPAT;	2004/05/18	
1 1	L8		5	(ion add implant)	US-PGPUB	18:27	
			, ,	(ion adj implant) with (nucleat\$)	USPAT;	2004/05/18	
_		٠	110050	420 /4	US-PGPUB	19:09	
1.	1 .		119259	438/\$.ccls. or 257/\$.ccls.	USPAT;	2003/02/13	-
1 .					US-PGPUB	15:43	1
-	• •		12479	(Implanting implanted implant) with	USPAT;	10.40	
			į.	(nitrogen trifluoronitride ammonia		2003/02/14	
		1		(nitrous adj oxide) (nitric adj oxido)	US-PGPUB	10:59	
1			. }	"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2	'		1 .
		j		o" "no") "n.sub.3" "n.sub.2	· · · ·		1
.] -			13765	(implanting implants)		•	ŀ
1	·	.	-3,03		USPAT;	2003/02/13	1 .
			, ,	(silicon (silicon adj tetrafluoride)	US-PGPUB	15:47	1.
			·	sliane dichlorosilane trichlorosilande			
	•	ľ		(Slilcon add tetrachloride) "sir sub 4"			
		1		SIH.SUD4" "SIH.Sub 2 cl sub 2"	, ,		
L_				"siCl.sub.3" "sicl.sub.4")			1
					. 1		1

(Implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "n.sub.2 " "sub.2" "nf.sub.3" "n.sub.2 " "sub.3" "n.sub.2 " "sub.3" "n.sub.2 " "sub.3" "n.sub.2 " "sid.sub.3" "sid.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4") (438/\$.ccls. or 257/\$.ccls.) and (silicon adj tetracfluoride) (silicon adj tetracfluoride) (silicon adj tetracfluoride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4")) (438/\$.ccls. or 257/\$.ccls.) and (silicon adj tetracfluoride) (silicon adj tetracfluoride) (silicon adj tetracfluoride) (silicon adj tetracfluoride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric.adj.oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 or "no"))) and (uniform near3 thickness\$ near3.dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) "siF.sub.4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3.dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon adj tetrachloride) "siF.sub.4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3.dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) (nitric adj oxide) (nitros adj ox	02/13
((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")) 11952 (438/\$.ccls. or 257/\$.ccls.) and (implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4") ((438/\$.ccls. or 257/\$.ccls.) and (implanting implanted implant) with (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) and (uniform near3 thickness\$ near3 dielectric) (438/\$.ccls. or 257/\$.ccls.) and (implanting implanted implant) with (nitrogen trifluoronitride ammonia (introus.adj.oxide) (nitric.adj.oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon adj tetrachlorosilande (silicon adj tetrafluoronitride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siC.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) (implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "n.sub.2" "n.sub.2" "n.sub.2" "n.sub.2" "n.sub.3" "n.sub.2 o" "n.sub.2" o" "n.sub.3" "n.sub.2 o" "n.sub.3" "n.sub.2 o" "n.sub.2" o" "n.sub.3" "n.sub.2 o" "n.sub.3" "n.sub.2 o" "n.sub.3" "n.sub.2 o" "n.sub.3" "n.sub.3 o" n.sub.3 o	02/13
(nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitros adj oxide) (nitros adj oxide) (nitrous adj	/02/13 / 02/13
(mitrous adj oxide) (mitric adj oxide) "n. sub.2" "nf. sub.3" "n. sub.2 oo" "no")) (438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF. sub.4" "siH. sub4" "siH. sub.2 cl. sub.2" "siCl. sub.3" "sicl. sub.4") 44 ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF. sub.4" "siH. sub4" "siH. sub.2 cl. sub.2" "siCl. sub.3" "sicl. sub.4")) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide).(nitric.adj.oxide) "n. sub.2" "nf. sub.3" "nh. sub.3" "n. sub.2 oo" "no"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF. sub.4" "siH. sub4" "siH. sub.2 cl. sub.2" "siCl. sub.3" "sicl. sub.4"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) "siF. sub4" "siH. sub.2 cl. sub.2" "siCl. sub.3" "sicl. sub.4"))) and (uniform near3 thickness\$ near3 dielectric) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n. sub.2" "nf. sub.3" "nl. sub.2" "siCl. sub.3" "nl. sub.3" "n. sub.2 oo" "no"))) and (uniform near3 thickness\$ near3 dielectric) 1 ("6465373").PN.	02/13
"n. sub.2" "nf. sub.3" "nh. sub.2 oo" "no")) (438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrafluoride) "siF. sub.4" "siH. sub4" "siH. sub.2 cl. sub.2" "siCl. sub.3" "sicl. sub.4")) (438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF. sub.4" "siH. sub4" "siH. sub.2 cl. sub.2" "siCl. sub.3" "sicl. sub.4"))) and (uniform near3 thickness\$ near3 dielectric) 12 ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide). "n. sub.2" "nf. sub.3" "nh. sub.3" "n. sub.2 oo" "no"))) and (uniform near3 thickness\$ near3 dielectric) 35 (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrafluoride) "siF. sub.4" "siH. sub4" "siH. sub.2 cl. sub.2" "siCl. sub.3" "siCl. sub.4")) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n. sub.2" "nf. sub.3" "nh. sub.3" "n. sub.2 oo" "no"))) and (uniform near3 thickness\$ near3 dielectric)) not (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n. sub.2" "nf. sub.3" "nh. sub.3" "n. sub.2 oo" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN.	02/13
o" "no")) (438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) (438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) and (uniform near3 thickness\$ near3 dielectric) (438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous.adj,oxide) (nitric.adj.oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$, near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$, near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nlb.sub.3" "n.sub.2 o" "no")) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/(USPAT; 2003/(US	02/13
(438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.3" "sicl.sub.4")) (438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "siCl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) 35 (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "fi.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/(02/13
((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) 44 ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrafluoride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) 12 ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide). "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) 35 (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (implanting implanted implant) with (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "n.sub.2 o" "no")))) and (uniform near3 thickness\$ near3 dielectric)) not ((6465373").pN. USPAT; 2003/01/201/201/201/201/201/201/201/201/201/	02/13
(silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4")) 44 ((a38/s.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3.dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nn.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) 1 ("6465373").PN. USPAT; 2003/(USPAT; 2003/(USPAT; 2003/(USPAT; 2003/(USPAT; 2003/(USPAT; 2003/(USPAT; 2003/(USPAT; 2003/(02/13
(\$111con (\$111con adj tetrafluoride) silane dichlorosilande trichlorosilande (\$111con adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4")) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous.adj oxide) (nitric.adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3.dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) 1 ("6465373").PN. USPAT; 2003/0	02/13
Silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4"	02/13
(\$111con adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4")) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "sicl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n. sub.2" "nf. sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$,ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	02/13
"SiH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) 44 ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrachloride) siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.)) and ((implanting implanted implant) with (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.)) and ((implanting implanted implant) with (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.2" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) 1 ("6465373").PN. USPAT; 2003/0	02/13
"siCl.sub.3" "sicl.sub.4")) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj oxide)(nitric.adj.oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	02/13
((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric.adj.oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. USPAT;	02/13
((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj.oxide).(nitric.adj.oxide). "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3.dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) not ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) not ((6189.4) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) not (1089.4) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) not (1089.4) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric))	02/13
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Silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj oxide).(nitric adj. oxide). "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "fi.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) not ((1000 million) not (1000 mi	
(silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and (implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "sicl.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and (implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "inf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) (""no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN.	
"siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrous adj.oxide) (nitric adj.oxide) "n.sub.2" "nf.sub.3" "nh.sub.2" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.)) and ((implanting implanted implant) with (silicon (silicon adj.tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj.tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.)) and ((implanting implanted implant) with (nitrous adj.oxide) (nitric adj.oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ""no"))) and (uniform near3 thickness\$ near3 dielectric)) """no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. USPAT; 2003/0	, .
"siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric) ((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous.adj.oxide)." "n.sub.2" "n.sub.2" "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous.adj.oxide) (nitric.adj.oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. USPAT; 2003/0	
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((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "sicl.sub4" "siH.sub.2 cl.sub.2" "sicl.sub3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. USPAT; 2003/0	00 (10
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o" "no")) and (uniform near3 thickness\$ near3 dielectric) (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	and the suppose of Annihold and a single of the suppose of the sup
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((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. US-PGPUB 16:34 16:34	12/13
(silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. USPAT; 2003/0	
silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.)) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. USPAT; 2003/0	£* 1
(silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.)) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. USPAT; 2003/0	
"siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
"siCl.sub.3" "sicl.sub.4"))) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
(((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
(nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) ("6465373").PN. USPAT; 2003/0	-
(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) and (uniform near3 thickness\$ near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
near3 dielectric)) 1 ("6465373").PN. USPAT; 2003/0	
- 1 ("6465373").PN. USPAT; 2003/0	
1 ("6465373").PN. USPAT; 2003/0	
OSFAI, 2003/(
	2/13
US-PGPUB 16:35	
USPAT; 2003/0	2/13
implanted implant)	
1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
((implanting implanted implant) with US_DCDUD 17 46	-, +-
(nitriding nitridization))	
4 RTN with (implanting implanted implant USDAM 6000 (6	0 (1 0
	2/13
255833 Canacitor DRAM 05-FGPOB 17:47	
USPAT; 2003/0	
- 122 (capacitor DRAM) and (((implanting US-PGPUB 10:54	2/14
implanted) With (angle)) same lie norm	
\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
(nitrous adj oxide) (nitric adj oxide)	
"n.sub.2" "nf.sub.3" "nh sub.3" "n sub.2	
[
132 (capacitor DRAM) and (((implanting USDAM)	
1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	2/14
same (nitrogen trifluoronitride ammonia US-PGPUB 15:45	2/14
I will to to dell till inoroni tride ammonia	2/14
(nitrous adj oxide) (nitric adj oxide)	2/14
"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2	2/14
(no)	2/14

	Γ					
			10		USPAT;	2003/02/14
				implant implanted) with (angle angled))	US-PGPUB	15:07
	-	İ		same (nitrogen trifluoronitride ammonia		
				(nitrous adi oxide) (nitric adi oxide)		
	;	-		"n.sub.2" "nf.sub.3" "nh.sub.3" "n sub.2		
		İ		(capacitor DRAM) and	.	
	}			(((Implanting implant implanted) with		
	1 .			(angle)) same (nitrogen trifluoronitride		
				ammonia (nitrous adi oxide) (nitric adi		
				oxide) "n.sub.2" "nf.sub.3" "nh sub 3"		
				("n.sub.2 o" "no")))		
	-		34	(capacitor DRAM) and (((doping doped	USPAT;	2003/02/14
		- 1		dope with (angle angled) same (nitrogen	US-PGPUB	
	!			Trilluoronitride ammonia (nitrous adi	US-FGFUB	14:04
٠,		ŀ		Oxide) (nitric adi oxide) "n sub 2"		
		1 .		"nr.sub.3" "nh.sub.3" "n.sub.2 o" "no"))		
	-	•	242	(Capacitor DRAM) and (((implanting	USPAT;	2004/05/17
				implant implanted) with (angle angled))	US-PGPUB	2004/05/17
	•	,	. ,	same (silicon (silicon adi tetrafluorida)	03-PGPUB	14:27
ı		1		silane dichlorosilane trichlorosilande		1
- 1				(SlilCon add tetrachloride)		
		1		"siH.sub4" "siH.sub.2 cl sub 2"		
		ŀ		"siCl.sub.3" "sicl.sub.4"))		1 - "
	-	. .	15	((capacitor DRAM) and ((doping doped	USPAT;	2002/02/24
		1		dope) with (angle angled)) same (nitrogen	US-PGPUB	2003/02/14
				trifluoronitride ammonia (nitrous adj	02-PGP0B	14:06
-1		1 -		oxide) (nitric adj oxide) "n.sub.2"		
		1		"nf.sub.3" "nh.sub.3" "n.sub.2.0" "no")))		
- 1		'		not ((capacitor DRAM) and (((implanting		
- [. [٠.	implant implanted) with (angle angled))		1 2 2 2
				same (nitrogen trifluoronitride ammonia	'	
	*			(nitrous adj oxide) (nitric adj oxide)		
İ				"n.sub.2" "nf.sub.3" "nh sub.3" "n gub.2		1
		100	7	o" "no")))		
	-	1	170	((capacitor DRAM) and (((implanting	Hanne	
- [1		implant implanted) with (angle angled))	USPAT;	2003/02/14
		1 :		same (silicon (silicon adj tetrafluoride)	US-PGPUB	14:46
.				silane dichlorosilane trichlorosilande		
-1		1.		(silicon adj tetrachloride) "siF.sub.4"		
1		ŀ		"siH.sub4" "siH.sub.2 cl.sub.2"		
		1		"siCl.sub.3"		
				((capacitor DRAM) and (((implanting		
1	٠			implant implanted) with (angle angled))	·	
		-		same (nitrogen trifluoronitride ammonia		ļ ļ.
	_			(nitrous adi oxide) (nitric adi ovido)		
				"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2		
				o" "no")))		
'	-	1	180	(capacitor DRAM), and (((implanting	USPAT;	2022/22/2
1				implant implanted) same (angle angled))	US-PGPUB	2003/02/14
1.	. ,			same (nitrogen trifluoronitride ammonia	ON-LGLOR	15:22
	•	-1	.	(nitrous adj oxide) (nitric adj oxide)	,	
1	8.1			"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2	j	
1	• .	•		o" "no"))		
-		1	27	(uniform uniformity) with ((silicon adj	USPAT;	2002/00/14
		ļ		nitride) "si.sub.3 N.sub.4") with	US-PGPUB	2003/02/14
		i	,	(implanting implanted doped doping doped	OB-PGPUB	14:49
1				implant)	1	
-	- · .	1	58	((capacitor DRAM) and (((implanting	USPAT;	2002/00/14
		i	.	implant implanted) same (angle angled))	US-PGPUB	2003/02/14
				same (nitrogen trifluoronitride ammonia	03-FGF0B	15:04
			,	(nitrous add oxide) (nitric add oxide)	.	
			1	"n.sub.2" "nf.sub.3" "nh sub 3" "n sub 2		ŀ
l			.	O no))) not ((capacitor DRAM) and		, ••
1.		•		(((Implanting implant implanted) with	,	
				(angle)) same (nitrogen trifluoropitride	,	
			- , - 	ammonia (nitrous adi oxide) (nitric adi		- 1
			- 1	OXIGE) "n.sub.2" "nf sub 3" "nb sub 2"		
L				"n.sub.2 o" "no")))		

٠.		_		**	1 - 1 - 2 - 2 - 2 - 2 - 2 - 2 - 2 - 2 -
į		1.	35 (capacitor DRAM) and (((doping doped	TICDAM :	1 2002 /00 /1
			dope) same (angle angled)) same (nitrogen	USPAT;	2003/02/14
		1	trifluoronitride ammonia (nitrous adj	US-PGPUB	15:17
			oxide) (nitric adj oxide) "n.sub.2"		.
			"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))		+
	-	30	(capacitor DRAM) and (((implanting		
		1	implant implanted) same (angle angled))	USPAT;	2003/02/14
			same (silicon (silicon adj tetrafluoride)	US-PGPUB	15:20
			silane dichlorosilane trichlorosilande		
			(silicon adj tetrachloride) "siF.sub.4"		
			"siH.sub4" "siH.sub.2 cl.sub.2"		
1	,*		"siCl.sub.3" "sicl.sub.4"))	.*	
	-	1 2	1 ((capacitor DRAM) and ((//implanting		
			TI TOWN AND TO THE DIGHT AND AND THE	USPAT;	2003/02/14
			implant implanted) same (angle angled))	US-PGPUB	15:14
			same (silicon (silicon adj tetrafluoride)		
			silane dichlorosilane trichlorosilande		
			(silicon adj tetrachloride) "siF.sub.4"		
1			"siH.sub4" "siH.sub.2 cl.sub.2"		
	•		"siCl.sub.3" "sicl.sub.4"))) not		
-	•		(((capacitor DRAM) and (((implanting		
			implant implanted) with (angle angled))		
			same (silicon (silicon adj tetrafluoride)		
1	and the second		silane dichlorosilane trichlorosilande		1
1			(silicon adj tetrachloride) "siF.sub.4"		
- :			"siH.sub4" "siH.sub.2 cl.sub.2"		.
		1 "	"siCl.sub.3" "sicl.sub.4"))) ((capacitor	· e	
ŀ			DRAM) and (((Implanting implant	•	
1	A		implanted) with (angle)) same (nitrogen	·	
			trifluoronitride ammonia (nitrous adj		
1		,	oxide) (nitric adj oxide) "n.sub.2"	, ,	
-	4.2		"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))		
			(((capacitor.DRAM) and (((implanting		
	State of the		implant implanted) same (angle angled))		
1			same (nitrogen trifluoronitride ammonia		
1		•	(nitrous adj oxide) (nitric adj oxide)		
l			"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2		
l		1.7	O "NO"))) not ((capacitor DRAM) and -		
١.		. *	(((implanting implant implanted) with		
'	•		(angle)) same (nitrogen trifluoronitrido		
ĺ		. *	ammonia (nitrous adj oxide) (nitric adj	4. 4	
	•		oxide) "n.sub.2" "nf.sub.3" "nh.sub.3"		
١.		1	"n.sub.2 o" "no")))))	4.	
١.		· · 1	("6326277").PN.	USPAT;	2003/02/14
١.	_	1	//// 622 6277//	US-PGPUB	15:14
		4		USPAT;	2003/02/14
		. 211	nitride)	US-PGPUB	15:15
		311		USPAT;	2003/02/14
	*	•	dope) same (angle angled)) same (silicon	US-PGPUB	15:19
			(Slilcon ad) tetrafluoride) silane		
			dichlorosilane trichlorosilande (silicon		
			adj tetrachloride) "siF.sub.4" "siH.sub4"		
,			"siH.sub.2 cl.sub.2" "siCl.sub.3"	* * * * * * * * * * * * * * * * * * *	
_	_	203	"sicl.sub.4"))		
		203		USPAT;	2003/02/14
	• 1		dope) same (angle angled)) same (silicon	US-PGPUB	15::20
			(silicon adj tetrafluoride) silane		
	`. '.	V -	dichlorosilane trichlorosilande (silicon		
	·	•	adj tetrachloride), "siF.sub.4" "siH.sub4"		
		•.	"siH.sub.2 cl.sub.2" "siCl.sub.3"		
			"sicl.sub.4"))) not ((capacitor DRAM) and	7.	
	, 1	-	((Limpranting implant implanted) same	,	
			(angle angled)) same (silicon (silicon	. [*
٠.			adj tetrafluoride) silane dichlorosilane		
•			UTICHIOTOSILande (silicon adi		
•	**	· '	tetrachloride) "siF.sub.4" "siH.sub4"		,
			"siH.sub.2 cl.sub.2" "siCl.sub.3"		
-		· · · · · · · · · · · · · · · · · · ·	"sicl.sub.4")))		
			· · · · · · · · · · · · · · · · · · ·		

				
- ,	7	4 ((capacitor DRAM) and (((doping doped	USPAT;	2003/02/14
ļ		dope same (angle angled) same (nitroger	US-PGPUB	
		trifluoronitride ammonia (nitrous adj	1 05-FGFUB	15:21
*	"	oxide) (nitric adj oxide) "n.sub.2"		
·	.:	"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))		1
	ļ,	not //sana-it = not //sana-it		
		not ((capacitor DRAM) and (((implanting		
1	1 1	implant implanted) same (angle angled))		
		same (nitrogen trifluoronitride ammonia		
		(nitrous adj oxide) (nitric adj oxide)	,	
		"n.sub.2" "nf.sub.3" "nh sub 3" "n sub 3		
		o" "no")))	, ,	
_	20	3 (((capaciton DDAM) and (())		
			USPAT;	2003/02/14
	· ·	dope) same (angle angled)) same (silicon	US-PGPUB*	15:23
		(silicon adj tetrafluoride) silane		
		dichlorosilane trichlorosilande (silicon		,
j		[ad] tetrachloride) "siF.sub 4" "siH sub4"		* ,
		"siH.sub.2 cl.sub.2" "siCl.sub.3"	-	1
	· /-	"sicl.sub.4"))) not ((capacitor DRAM) and		
		(//implemental) not ((Capacitor DRAM) and		
		(((implanting implant implanted) same		
		(angle angled)) same (silicon (silicon		
	,	ad] tetrafluoride) silane dichlorosilane	+ :	1 1 1 2
		trichlorosilande (silicon adi	1	1 .
		tetrachloride) "siF.sub.4" "siH.sub4"		
1		"siH.sub.2 cl.sub.2" "siCl.sub.3"	1	
1		"sicl sub 4"\\\\		1
		"sicl.sub.4")))) not ((capacitor_DRAM)		
		and (((Implanting implant implanted) with		
		(angle angled)) same (silicon (silicon		
·	1	ad] tetrafluoride) silane dichlorosilano		1 .
		trichlorosilande (silicon adj		
		tetrachloride) "siF.sub.4" "siH.sub4"		
	:	"siH sub 2 al aut 0" "siH. sub4"		
		"siH.sub.2 cl.sub.2" "siCl.sub.3"		
	100	"sicl.sub.4")))		
 	198	The state of the s	USPAT;	2003/02/14
		dope same (angle angled) same (silicon	US-PGPUB	
		(Silicon add tetrafluoride) silane	OS FGFOD	15:24
		dichlorosilane trichlorosilande (silicon		
	1.00	adj tetrachloride) "siF.sub.4" "siH.sub4"		
		"siH sub 2 sl sub 2" "SIH. Sub4"		
	1	"siH.sub.2 cl.sub.2" "siCl.sub.3"		+
ì,		"sicl.sub.4"))) not ((capacitor DRAM) and		
	*	(((Implanting implant implanted) same		
		(angle angled)) same (silicon (silicon	1	
		ad tetrafluoride) silane dichlorosilano		
		trichlorosilande (silicon adj		
1 " "	1	tetrachloride) "siF.sub.4" "siH.sub4"	1 1	
-		"siH.sub.2 cl.sub.2" "siCl.sub.3"		1
	1	"sicl sub 4"\\\\		
		"sicl.sub.4"))))) not ((capacitor DRAM)		
		and (((Implanting implant implanted) same		
1		(angle angled)) same (nitrogen		1.
		trifluoronitride ammonia (nitrous adi	l. '	
		OXIGE) (nitric adi oxide) "n sub 2"		in the second second
		"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))		
1 -	1	09/385787 III.Sub.3 II.Sub.2 o" "no")))		
1 :	1.	72,000,01	USPAT;	2003/02/14
_	1	/!! 61 5 0 7 0 5 11 2 2 2 2	US-PGPUB	15:32
;	1	("6159785").PN.	USPAT;	2003/02/14
			US-PGPUB	15:32
1 -	1	(("6159785").PN.) and (silicon adj		
1	.['	nitride)	UC DODGE	2003/02/14
-	1 3	(capacitor DRAM) and (((implanting	US-PGPUB	15:32
1		implant implanted done done		2003/02/14
	1.	implant implanted dope doping doped) with		15:47
	1.	(angle angled)) same (nitrogen "si.sub.3		·
1_	1	[II.SUD.4] Same (uniformity uniform))		·
	1	("6204142").PN.	USPAT;	2004/05/17
l - ,	7641	(Shin).in.		16:46
l	' -			2004/05/17
-	1	"20010018787"		16:46
	_		USPAT;	2004/05/17
				16:46
**				

	- '	11 (("4963506") or ("5663087") or	USPAT;	2004/05/17	Т
	*.	("5882978") or ("5939333") or ("5981404")	US-PGPUB	17:59	l
j		or ("6077754") or ("6147013") or	' '	-,,,,,	
	•	("6171977") or ("6258690") or ("6268299")	<i>:</i>		١.
L		or ("6284583")).PN.		·	